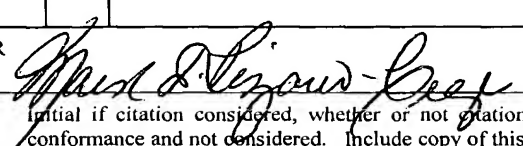


#4 IDS

Sheet 1 of 1

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 111779		APPLICATION NO. New U.S. Patent Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Akihiko EBINA, Yutaka MARUO			
				FILING DATE January 23, 2002			
<div style="float: right; text-align: right;"> J1046 U.S. PTO 10/052549 01/23/02 </div>							
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
X	1	New U.S. Patent Application (Atty. docket # 111778)	01/23/2002	Ebina et al.			
MSP	2	6,255,166 B1	07/03/2001	Ogura et al.			
MSP	3	5,408,115	04/18/1995	Chang			
MSP	4	5,969,383	10/19/1999	Chang et al.			
MSP	5	5,422,504	06/06/1995	Chang et al.			
MSP	6	5,494,838	02/27/1996	Chang et al.			
MSP	7	6,177,318 B1	01/23/2001	Ogura et al.			
MSP	8	6,248,633 B1	06/19/2001	Ogura et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
X	9	JP B1 2978477 (w/English translation)	09/10/1999	Japan			
MSP	10	JP A 7-161851 (w/English translation)	06/23/1995	Japan			
MSP	11	JP A 2001-156188 (w/English translation)	06/08/2001	Japan			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
MSP	12	Hayashi et al., "Twin MONOS Cell with Dual Control Gates", IEEE VLSI Technology Digest, 2000.					
MSP	13	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE ELECTRON DEVICE LETTERS, Vol. 19, No. 7, July 1998, pp. 253-255.					
MSP	14	Chen et al., "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN)", VLSI Technology Digest, pp. 63-64, 1997.					
EXAMINER					DATE CONSIDERED 11/23/2002		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							